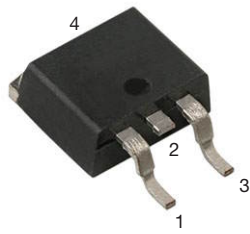
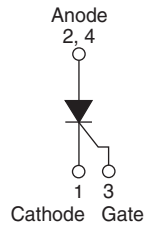


Thyristor, Surface Mount, Phase Control SCR, 16 A


D²PAK (TO-263AB)


FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
 COMPLIANT
 HALOGEN
FREE

PRIMARY CHARACTERISTICS

$I_{T(AV)}$	16 A
V_{DRM}/V_{RRM}	1200 V
V_{TM}	1.25 V
I_{GT}	45 mA
T_J	-40 to +125 °C
Package	D ² PAK (TO-263AB)
Circuit configuration	Single SCR

APPLICATIONS

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-25TTS12SLHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS

APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5	A
Aluminum IMS, $R_{thCA} = 15$ °C/W	8.5	13.5	
Aluminum IMS with heatsink, $R_{thCA} = 5$ °C/W	16.5	25.0	

Note

- $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	16	A
I_{RMS}		25	
V_{RRM}/V_{DRM}		1200	V
I_{TSM}		350	A
V_T	16 A, $T_J = 25$ °C	1.25	V
dV/dt		500	V/μs
dI/dt		150	A/μs
T_J		-40 to +125	°C

VOLTAGE RATINGS

PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM} / I_{DRM} , AT 125 °C mA
VS-25TTS12SLHM3	1200	1200	10



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS	
			TYP.	MAX.		
Maximum average on-state current	$I_{T(AV)}$	$T_C = 93\text{ }^\circ\text{C}$, 180° conduction half sine wave	16		A	
Maximum RMS on-state current	I_{RMS}		25			
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	300			
		10 ms sine pulse, no voltage reapplied	350			
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	450		A^2s	
		10 ms sine pulse, no voltage reapplied	630			
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to }10\text{ ms}$, no voltage reapplied	6300		$A^2\sqrt{s}$	
Maximum on-state voltage drop	V_{TM}	16 A, $T_J = 25\text{ }^\circ\text{C}$	1.25		V	
On-state slope resistance	r_t	$T_J = 125\text{ }^\circ\text{C}$	12.0		$m\Omega$	
Threshold voltage	$V_{T(TO)}$		1.0		V	
Maximum reverse and direct leakage current	I_{RM} / I_{DM}	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	0.5		mA
		$T_J = 125\text{ }^\circ\text{C}$		10		
Holding current	I_H	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$, $T_J = 25\text{ }^\circ\text{C}$	-	150	
				200		
Maximum latching current	I_L	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	200			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J\text{ max.}$, linear to 80 %, $V_{DRM} = R_g - k = \text{open}$	500		$V/\mu s$	
Maximum rate of rise of turned-on current	di/dt		150		$A/\mu s$	

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	$+I_{GM}$		1.5	A
Maximum peak negative gate voltage	$-V_{GM}$		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	60	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	45	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	20	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	2.5	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	2.0	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	1.0	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^\circ\text{C}$, $V_{DRM} = \text{rated value}$	0.25	
Maximum DC gate current not to trigger	I_{GD}		2.0	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^\circ\text{C}$	0.9	μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^\circ\text{C}$	4	
Typical turn-off time	t_q		110	



THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-40 to +125	°C
Soldering temperature	T_S	For 10 s (1.6 mm from case)	260	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.1	°C/W
Typical thermal resistance, junction to ambient (PCB mount)	$R_{thJA}^{(1)}$		40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D ² PAK (TO-263AB)	25TTS12SH	

Note

(1) When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W

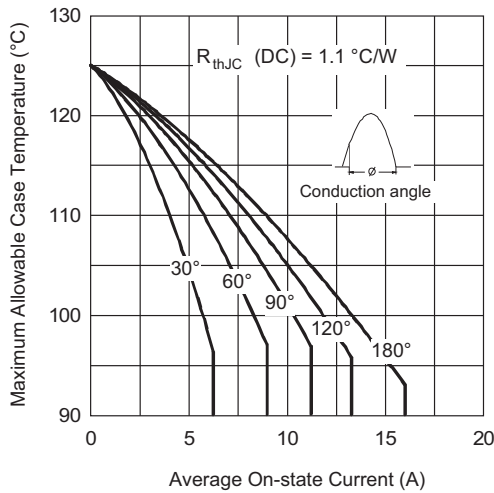


Fig. 1 - Current Rating Characteristics

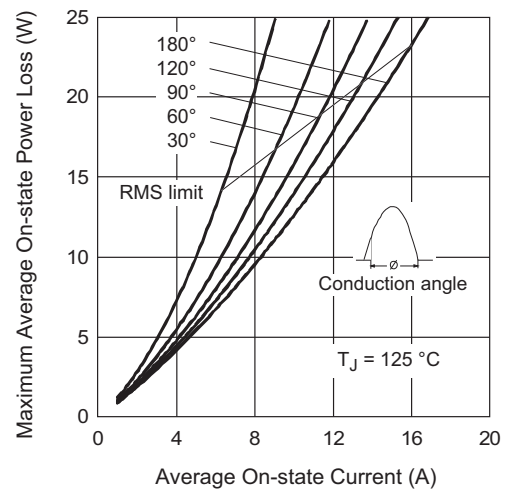


Fig. 3 - On-State Power Loss Characteristics

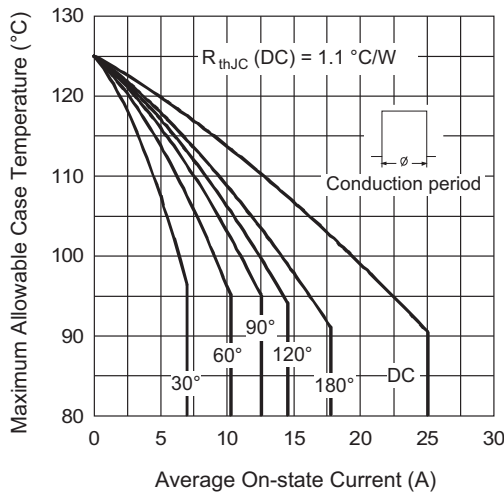


Fig. 2 - Current Rating Characteristics

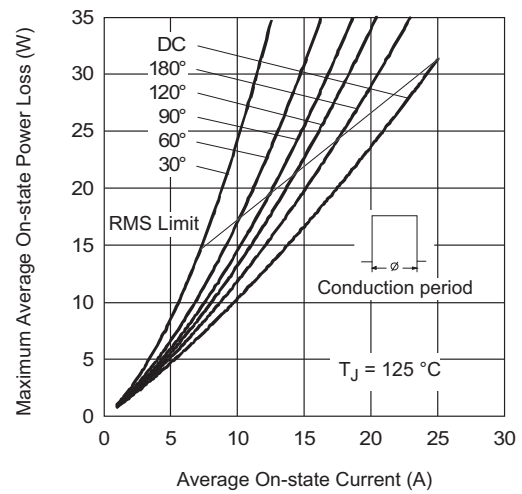


Fig. 4 - On-State Power Loss Characteristics

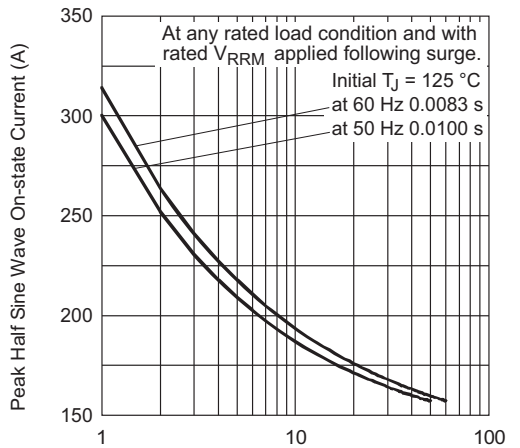


Fig. 5 - Maximum Non-Repetitive Surge Current

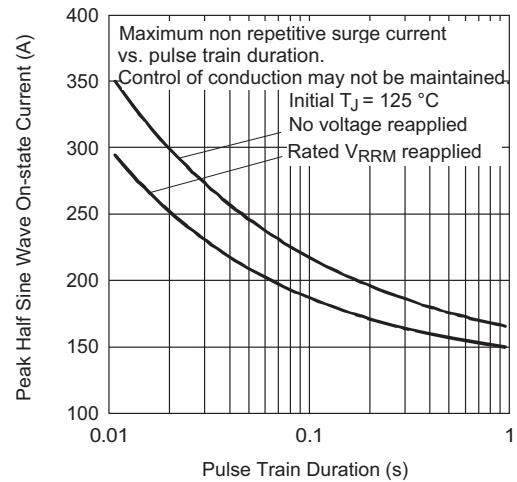


Fig. 6 - Maximum Non-Repetitive Surge Current

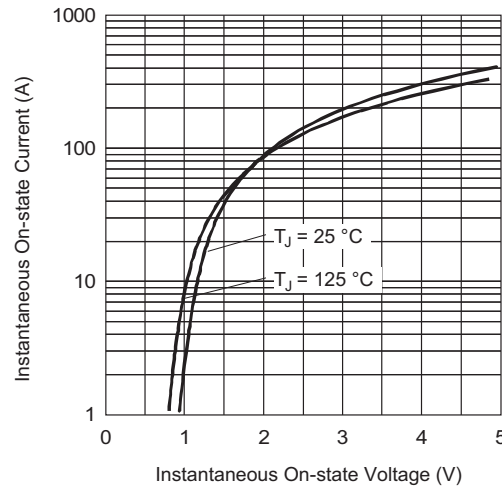


Fig. 7 - On-State Voltage Drop Characteristics

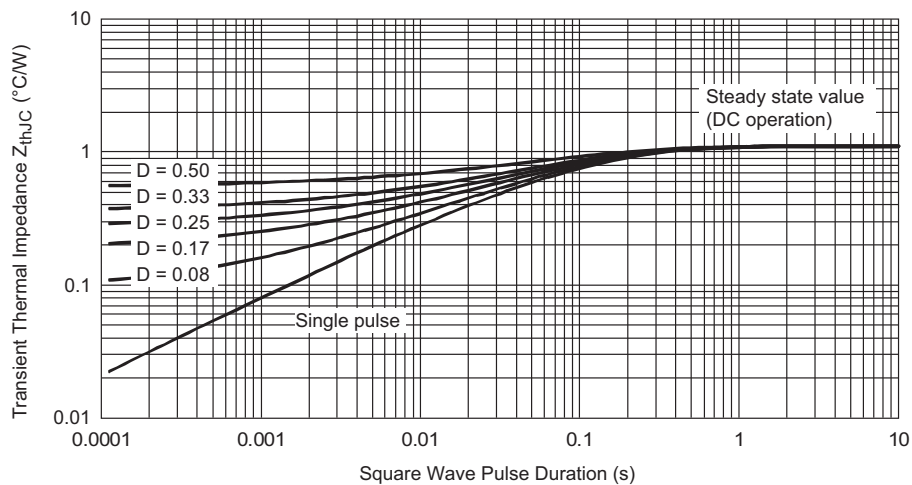
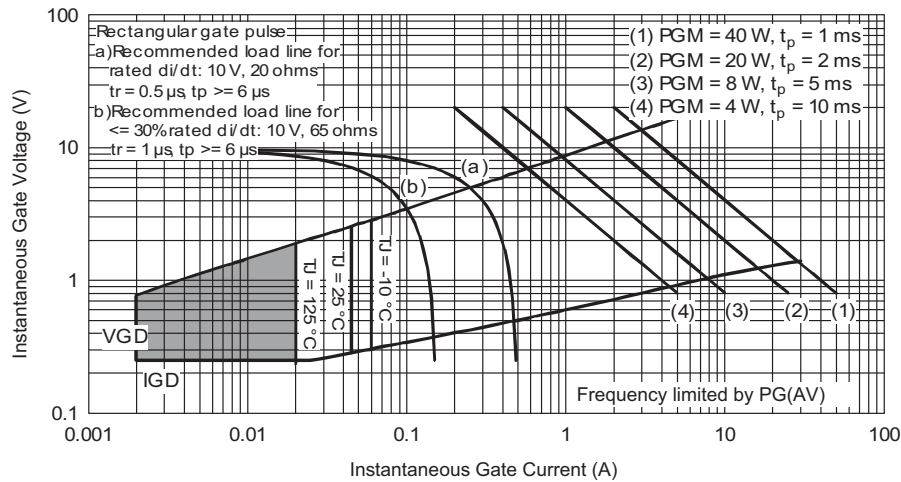


Fig. 8 - Gate Characteristics


 Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	25	T	T	S	12	S	L	H	M3
	①	②	③	④	⑤	⑥	⑦	⑧	⑨	⑩

- 1** - Vishay Semiconductors product
- 2** - Current rating (25 = 25 A)
- 3** - Circuit configuration:
T = single thyristor
- 4** - Package:
T = D²PAK (TO-263AB)
- 5** - Type of silicon:
S = standard recovery rectifier
- 6** - Voltage rating: voltage code x 100 = V_{RRM} ——— **12 = 1200 V**
- 7** - S = surface mountable
- 8** - L = tape and reel (left oriented), for different orientation contact factory
- 9** - H = AEC-Q101 qualified
- 10** - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-25TTS12SLHM3	800	800	13" diameter reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95046
Part marking information	www.vishay.com/doc?95444
Packaging information	www.vishay.com/doc?96317

D²PAK

DIMENSIONS in millimeters and inches

Conforms to JEDEC® outline D²PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

- Dimensioning and tolerancing per ASME Y14.5 M-1994
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- Thermal pad contour optional within dimension E, L1, D1 and E1
- Dimension b1 and c1 apply to base metal only
- Datum A and B to be determined at datum plane H
- Controlling dimension: inch
- Outline conforms to JEDEC® outline TO-263AB



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